Journal of Crystal Growth 121 (1992) 796–801
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Akiya, K., see Goto 121 (1992) 360
Albrecht, M., see Hansson 121 (1992) 790
Al-Dhahir, T.A., G. Dhanaraj and H.L. Bhat, Growth of alkali metal periodates from silica gel and their characterization 121 (1992) 132
Alibert, C., see Mani 121 (1992) 463
Amelinckx, S., W. Luyten, T. Krekels, G. Van Tendeloo and J. Van Landuyt, Conical, helically wound, graphite whiskers: a limiting member of the "fullerenes"? 121 (1992) 543
Aubin, M., see Gagnon 121 (1992) 559

Babić-Ivancić, V., see Skrtić 121 (1992) 197
Babinský, M., see Korytár 121 (1992) 440
Bachem, K.-H., see Stöber 121 (1992) 656
Bamzai, K., A.K. Razdan, P.N. Kotru and B.M. Wanklyn, Dislocation etchants for flux grown $YFeO_3$ single crystals 121 (1992) 519
Baugher, C., see Naumann 121 (1992) 751
Bauser, E., see Lu 121 (1992) 566
Bauser, E., see Hansson 121 (1992) 790
Beccard, R., S. Beuven, K. Heime, R. Schmald, H. Jürgensen, P. Harde and M. Schlak, Growth of semi-insulating InP:Fe in the low pressure hydride VPE system 121 (1992) 373
Beda, P., J.C. Han and S. Motakef, Application of strong vertical magnetic fields to growth of II–VI pseudo-binary alloys: HgMnTe 121 (1992) 394
Bennema, P., see Cherepanova 121 (1992) 1
Bennema, P., see Cherepanova 121 (1992) 17
Bennema, P., Xiang Yang Liu, K. Lewtas, R.D. Tack, J.J.M. Rijpkema and K.J. Roberts, Morphology of orthorhombic long chain normal alkanes: theory and observations 121 (1992) 679
Bennema, P., see Vogels 121 (1992) 697
Benz, K.W., see Danilewsky 121 (1992) 305
Bergmann, R., see Hansson 121 (1992) 790
Beuven, S., see Beccard 121 (1992) 373
Bhat, H.L., see Al-Dhahir 121 (1992) 132
Bhat, H.L., see Elizabeth 121 (1992) 531
Bhat, H.L., R.I. Ristić, J.N. Sherwood and T. Shripathi, Dislocation characterization in crystals of potash alum grown by seeded solution growth under conditions of low supersaturation 121 (1992) 709
Bhat, S.V., see Elizabeth 121 (1992) 531
Billia, B., see Grange 121 (1992) 315
Binnewies, M., see Stöber 121 (1992) 656
Boeck, T., see Wermke 121 (1992) 571
Boistelle, R., see Lopez-Valero 121 (1992) 297
Bosnell, J., see Gerrard 121 (1992) 500
Bostanov, V., see Obretenov 121 (1992) 495
Böttner, H., see Stöber 121 (1992) 656
Brandon, S. and J.J. Derby, Heat transfer in vertical Bridgman growth of oxides: effects of conduction, convection, and internal radiation 121 (1992) 473
Brebner, J.L., see Tran 121 (1992) 365
Brich, J., see Håkansson 121 (1992) 399
Brown, R.A., see Lee 121 (1992) 536

Carlsson, J.-O., see Lampe-Önnerud 121 (1992) 223
Chai Yiao, see Pan 121 (1992) 141
Chang, Y.H., see Yang 121 (1992) 717
Chen, Baijun, see Meng 121 (1992) 191
Chen, L.J., C.C. Wan and C. Lien, Simulation of the growth rate and layer thickness for liquid phase epitaxy (LPE) under slider-induced convection 121 (1992) 322
Chen, W.J., see Yang 121 (1992) 717
Cherepanova, T.A., P. Bennema, Yu.A. Yanson and K. Tsukamoto, Advance velocities of steps on {211} and {110} faces of yttrium iron garnet: theory and observations 121 (1992) 1
Cherepanova, T.A., P. Bennema, Yu.A. Yanson and L.J.P. Vogels, Morphology of synthetic and natural garnets: theory and observations 121 (1992) 17
Chernov, A.A., see Vekilov 121 (1992) 44
Chernov, A.A., see Vekilov 121 (1992) 643
Christoffersen, J. and M.R. Christoffersen, A revised theory for the growth of crystals by surface nucleation 121 (1992) 608
Christoffersen, J., see Christoffersen 121 (1992) 617
Christoffersen, M.R., see Christoffersen 121 (1992) 608
Christoffersen, M.R., and J. Christoffersen, Possible mechanisms for the growth of the biomaterial, calcium hydroxyapatite microcrystals 121 (1992) 617
Chung, C.K., see Yang 121 (1992) 717
Clark, S.A., J.E. Macdonald, D.I. Westwood and R.H. Williams, Relaxation in

Journal of Crystal Growth 121 (1992) 796–801
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Akiya, K., see Goto 121 (1992) 360
Albrecht, M., see Hansson 121 (1992) 790
Al-Dhahir, T.A., G. Dhanaraj and H.L. Bhat, Growth of alkali metal periodates from silica gel and their characterization 121 (1992) 132
Alibert, C., see Mani 121 (1992) 463
Amelinckx, S., W. Luyten, T. Krekels, G. Van Tendeloo and J. Van Landuyt, Conical, helically wound, graphite whiskers: a limiting member of the "fullerenes"? 121 (1992) 543
Aubin, M., see Gagnon 121 (1992) 559

Babić-Ivancić, V., see Skrtić 121 (1992) 197
Babinský, M., see Korytár 121 (1992) 440
Bachem, K.-H., see Stöber 121 (1992) 656
Bamzai, K., A.K. Razdan, P.N. Kotru and B.M. Wanklyn, Dislocation etchants for flux grown $YFeO_3$ single crystals 121 (1992) 519
Baugher, C., see Naumann 121 (1992) 751
Bauser, E., see Lu 121 (1992) 566
Bauser, E., see Hansson 121 (1992) 790
Beccard, R., S. Beuven, K. Heime, R. Schmald, H. Jürgensen, P. Harde and M. Schlak, Growth of semi-insulating InP:Fe in the low pressure hydride VPE system 121 (1992) 373
Beda, P., J.C. Han and S. Motakef, Application of strong vertical magnetic fields to growth of II–VI pseudo-binary alloys: HgMnTe 121 (1992) 394
Bennema, P., see Cherepanova 121 (1992) 1
Bennema, P., see Cherepanova 121 (1992) 17
Bennema, P., Xiang Yang Liu, K. Lewtas, R.D. Tack, J.J.M. Rijpkema and K.J. Roberts, Morphology of orthorhombic long chain normal alkanes: theory and observations 121 (1992) 679
Bennema, P., see Vogels 121 (1992) 697
Benz, K.W., see Danilewsky 121 (1992) 305
Bergmann, R., see Hansson 121 (1992) 790
Beuven, S., see Beccard 121 (1992) 373
Bhat, H.L., see Al-Dhahir 121 (1992) 132
Bhat, H.L., see Elizabeth 121 (1992) 531
Bhat, H.L., R.I. Ristić, J.N. Sherwood and T. Shripathi, Dislocation characterization in crystals of potash alum grown by seeded solution growth under conditions of low supersaturation 121 (1992) 709
Bhat, S.V., see Elizabeth 121 (1992) 531
Billia, B., see Grange 121 (1992) 315
Binnewies, M., see Stöber 121 (1992) 656
Boeck, T., see Wermke 121 (1992) 571
Boistelle, R., see Lopez-Valero 121 (1992) 297
Bosnell, J., see Gerrard 121 (1992) 500
Bostanov, V., see Obretenov 121 (1992) 495
Böttner, H., see Stöber 121 (1992) 656
Brandon, S. and J.J. Derby, Heat transfer in vertical Bridgman growth of oxides: effects of conduction, convection, and internal radiation 121 (1992) 473
Brebner, J.L., see Tran 121 (1992) 365
Brich, J., see Håkansson 121 (1992) 399
Brown, R.A., see Lee 121 (1992) 536

Carlsson, J.-O., see Lampe-Önnerud 121 (1992) 223
Chai Yiao, see Pan 121 (1992) 141
Chang, Y.H., see Yang 121 (1992) 717
Chen, Baijun, see Meng 121 (1992) 191
Chen, L.J., C.C. Wan and C. Lien, Simulation of the growth rate and layer thickness for liquid phase epitaxy (LPE) under slider-induced convection 121 (1992) 322
Chen, W.J., see Yang 121 (1992) 717
Cherepanova, T.A., P. Bennema, Yu.A. Yanson and K. Tsukamoto, Advance velocities of steps on {211} and {110} faces of yttrium iron garnet: theory and observations 121 (1992) 1
Cherepanova, T.A., P. Bennema, Yu.A. Yanson and L.J.P. Vogels, Morphology of synthetic and natural garnets: theory and observations 121 (1992) 17
Chernov, A.A., see Vekilov 121 (1992) 44
Chernov, A.A., see Vekilov 121 (1992) 643
Christoffersen, J. and M.R. Christoffersen, A revised theory for the growth of crystals by surface nucleation 121 (1992) 608
Christoffersen, J., see Christoffersen 121 (1992) 617
Christoffersen, M.R., see Christoffersen 121 (1992) 608
Christoffersen, M.R., and J. Christoffersen, Possible mechanisms for the growth of the biomaterial, calcium hydroxyapatite microcrystals 121 (1992) 617
Chung, C.K., see Yang 121 (1992) 717
Clark, S.A., J.E. Macdonald, D.I. Westwood and R.H. Williams, Relaxation in

$In_xGa_{1-x}As/InP$ for compressive and tensile strain 121 (1992) 743
Cotta, M.A. and M.M.G. de Carvalho, Monte Carlo simulation study on the flow conditions of a vacuum chemical epitaxy system 121 (1992) 429
Cova, P., see Tran 121 (1992) 365
Cui, Jie, Hailong Wang and Fuxi Gan, The optical and spectroscopic properties of II–VI wide-gap ZnSe/ZnS and ZnSe/ZnTe strained-layer superlattices (E) 121 (1992) 795

Dabholkar, V. and R. Pollard, A model for the dynamics of island growth during deposition of compound semiconductors 121 (1992) 71
Danilewsky, A.N., P. Dold and K.W. Benz, The influence of axial magnetic fields on the growth of III–V semiconductors from metallic solutions 121 (1992) 305
Daniška, V., see Korytár 121 (1992) 440
De Carvalho, M.M.G., see Cotta 121 (1992) 429
De Oliveira, A.G., see Ferguson 121 (1992) 267
Dentai, A.G., see Joyner 121 (1992) 413
Derby, J.J., see Brandon 121 (1992) 473
Devenyns, J.A.H., see Verbeeck 121 (1992) 335
Dhanaraj, G., see Al-Dhahir 121 (1992) 132
Dhanaraj, G., see Elizabeth 121 (1992) 531
Doerschel, J. and U. Geissler, Characterization of extended defects in highly Te-doped ⟨111⟩ GaSb single crystals grown by the Czochralski technique 121 (1992) 781
Dold, P., see Danilewsky 121 (1992) 305
Dong, Guang, see Meng 121 (1992) 191
Dutta, P.K., see Narlikar 121 (1992) 527

Elizabeth, S., G. Dhanaraj, S.V. Bhat and H.L. Bhat, Growth and extraction of flux free YBCO crystals 121 (1992) 531
Elliott, A.G., A. Flat and D.A. Vanderwater, Silicon incorporation in LEC growth of single crystal gallium arsenide 121 (1992) 349
Enami, H., see Hoshizaki 121 (1992) 53

Fan, X.W., see Zhang 121 (1992) 769
Ferguson, I.T., A.G. de Oliveira and B.A. Joyce, RHEED intensity effects during the growth of InAs, InSb and In(As, Sb) by molecular beam epitaxy 121 (1992) 267
Filipović-Vinceković, N., see Skrtić 121 (1992) 197
Flat, A., see Elliott 121 (1992) 349
Fujii, K., F. Orito, H. Fujita and T. Sato, The role of diffusion barrier temperature in gallium arsenide crystals grown by the gradient freeze method 121 (1992) 255
Fujita, H., see Fujii 121 (1992) 255
Furukawa, Y., see Goto 121 (1992) 360

Gagnon, R., M. Oussena and M. Aubin, Growth of $YBa_2Cu_3O_{7-x}$ crystals in thoria crucibles: twinning and optical effects 121 (1992) 559
Gali, S., see Sandiumenge 121 (1992) 247
Gan, Fuxi, see Cui 121 (1992) 795
Gastaldi, J., see Remy 121 (1992) 243
Gastaldi, J., see Grange 121 (1992) 315
Geissler, U., see Doerschel 121 (1992) 781
Gerrard, N.D., L.M. Smith, A.C. Jones and J. Bosnell, An improved method of trimethylindium transport for the growth of indium phosphide and related alloys by MOVPE 121 (1992) 500
Göbel, T., see Wermke 121 (1992) 571
Gomez-Lorente, C., see Lopez-Valero 121 (1992) 297
Goto, A., K. Akiya, T. Hondoh, Y. Furukawa, T. Shimura, I. Takahashi and J. Harada, Characterization of the (0001) surface of ice I_h crystal by crystal truncation rod scattering with the use of a synchrotron radiation source 121 (1992) 360
Grange, G., see Remy 121 (1992) 243
Grange, G., J. Gastaldi, C. Jourdan, P. Marzo and B. Billia, In situ observations by synchrotron white beam X-ray topography of the solidification microstructures of an Al–0.73 wt% Cu alloy 121 (1992) 315
Grugel, R.N., S. Kim, T. Woodward and T.G. Wang, The effect of axial crucible rotation on microstructural uniformity during horizontal directional solidification 121 (1992) 599
Gustafsson, A., see Hansson 121 (1992) 790

Håkansson, G., J. Birch, L. Hultman, I.P. Ivanov, J.-E. Sundgren and L.R. Wallenberg, Ion irradiation effects during growth of Mo/V(001) superlattices by dual-target magnetron sputtering 121 (1992) 399
Han, J.C., see Beda 121 (1992) 394
Hansson, P.O., A. Gustafsson, M. Albrecht, R. Bergmann, H.P. Strunk and E. Bauser, High quality Ge_xSi_{1-x} by heteroepitaxial lateral overgrowth 121 (1992) 790
Harada, J., see Goto 121 (1992) 360
Harde, P., see Beccard 121 (1992) 373
Hårsta, A., see Lampe-Önnerud 121 (1992) 223
Heime, K., see Beccard 121 (1992) 373
Higuchi, M., D. Miyauchi, A. Takeuchi and K. Kodaira, Hydrothermal growth of calcite single crystals from H_2O–CO_2–$CaCO_3$ system under controlled CO_2 pressure 121 (1992) 39
Hildmann, B.O., see Stöber 121 (1992) 656
Hondoh, T., see Goto 121 (1992) 360
Hoshizaki, H., S. Kawabata, N. Kawahara, H. Enami, T. Shinohara and T. Imura,

Direct observation of crystal growth and preparation of 2212-phase single crystals in Li-doped Bi–Sr–Ca–Cu–O system 121 (1992) 53
Hou, Guohua 121 (1992) 191
Hou Yinchun, see Pan 121 (1992) 141
Hsu, W.C., see Shieh 121 (1992) 665
Hultman, L., see Håkansson 121 (1992) 399
Hwang, J., see Yang 121 (1992) 717

Ichimura, M., Y. Moriguchi, A. Usami, T. Wada, M. Tabuchi and A. Sasaki, Micro-Raman study of heteroepitaxial InGaAs layers 121 (1992) 423
Iga, R., see Sugiura 121 (1992) 579
Imura, T., see Hoshizaki 121 (1992) 53
Inaoka, K., see Yase 121 (1992) 449
Inoue, T., see Yase 121 (1992) 449
Ishigaki, T., see Okada 121 (1992) 250
Ivanov, I.P., see Håkansson 121 (1992) 399
Iyi, N., see Yamamoto 121 (1992) 522
Izmailov, A.F. and A.S. Myerson, Concentration gradient formation in supersaturated vertical columns. I. Fokker–Planck approximation 121 (1992) 723

Jacobs, K., see Wermke 121 (1992) 571
Jansson, U., see Lampe-Önnerud 121 (1992) 223
Jones, A.C., see Gerrard 121 (1992) 500
Joullié, A., see Mani 121 (1992) 463
Jourdan, C., see Remy 121 (1992) 243
Jourdan, C., see Grange 121 (1992) 315
Joyce, B.A., see Ferguson 121 (1992) 267
Joyce, B.E., see Zhang 121 (1992) 381
Joyner, C.H., L.M. Ostar and A.G. Dentai, Exciton degradation due to group V interdiffusion in InGaAs/InP quantum wells during annealing or subsequent growth by MOVPE 121 (1992) 413
Jürgensen, H., see Beccard 121 (1992) 373

Kaito, C., see Yase 121 (1992) 449
Katsumata, T., H. Konoura, A. Konno, K. Takei, M. Shinohara and K. Takahashi; Moisture contents of $Li_2B_4O_7$ glass and single crystals 121 (1992) 737
Kawabata, S., see Hoshizaki 121 (1992) 53
Kawahara, N., see Hoshizaki 121 (1992) 53
Kim, H.K., see Suh 121 (1992) 417
Kim, J.M., see Suh 121 (1992) 417
Kim, J.S., see Suh 121 (1992) 417
Kim, S., see Grugel 121 (1992) 599
Kimura, S., see Yamamoto 121 (1992) 522
Kitamura, K., see Yamamoto 121 (1992) 522
Ko, E.I., see Snyder 121 (1992) 631
Kodaira, K., see Higuchi 121 (1992) 39
Komatsu, S., see Okada 121 (1992) 250
Konno, A., see Katsumata 121 (1992) 737
Konoura, H., see Katsumata 121 (1992) 737
Korytár, D., V. Daniška, I. Priecel and M. Babinský, Large-area X-ray and CL study of SI GaAs wafers from various suppliers 121 (1992) 440
Koshushkin, V.G., see Kozhemyakin 121 (1992) 240
Kotru, P.N., see Bamzai 121 (1992) 519
Kozhemyakin, G.N., V.G. Kosushkin and S.Y. Kurochkin, Growth of GaAs crystals pulled under the presence of ultrasonic vibrations 121 (1992) 240
Krekels, T., see Amelinckx 121 (1992) 543
Krost, A., see Wright 121 (1992) 111
Kurochkin, S.Y., see Kozhemyakin 121 (1992) 240
Kusakabe, K., see Maeda 121 (1992) 507
Kuznetsov, Yu.G., see Vekilov 121 (1992) 44
Kuznetsov, Yu.G., see Vekilov 121 (1992) 643
Kwak, N.J., see Suh 121 (1992) 417

Lambert, B., see Mani 121 (1992) 463
Lampe-Önnerud, C., U. Jansson, A. Hårsta and J.-O. Carlsson, Chemical vapour deposition of copper on Si(111) and SiO_2 substrates 121 (1992) 223
Launay, J.-C. and F. Lestournelle, Crystal growth by THM of $CdIn_2Te_4$ and chemical characterization 121 (1992) 202
Lazzari, J.L., see Mani 121 (1992) 463
Le Lay, G., see Remy 121 (1992) 243
Lee, J.T.C., K. Tsiveriotis and R.A. Brown, Spatiotemporal chaos near the onset of cellular growth during thin-film solidification of a binary alloy 121 (1992) 536
Leonelli, R., see Tran 121 (1992) 365
Lestournelle, F., see Launay 121 (1992) 202
Lewtas, K., see Bennema 121 (1992) 679
Li, L. and N. Rodríguez-Hornedo, Growth kinetics and mechanism of glycine crystals 121 (1992) 33
Li Zhengdog, Su Genbo and Wu Baichang, Growth and characterization of methyl p-hydroxybenzoate (p-MHB) 121 (1992) 516
Lien, C., see Chen 121 (1992) 322
Lifshits, V.G., see Zotov 121 (1992) 88
Lim, S.W., see Suh 121 (1992) 417
Liu, Xiang Yang, see Bennema 121 (1992) 679
Lopez-Valero, I., C. Gomez-Lorente and R. Boistelle, Effects of sodium and ammonium ions on occurrence, evolution and crystallinity of calcium phosphates 121 (1992) 297
Lu, Y.-C., E. Bauser and H.-J. Queisser, Thin epitaxial gallium aluminum arsenide layers grown by multi-compartment liquid-phase epitaxy 121 (1992) 566
Luyten, W., see Amelinckx 121 (1992) 543

Macdonald, J.E., see Clark 121 (1992) 743
Mackey, K.J., see Vere 121 (1992) 62

Maeda, H., S. Masuda, K. Kusakabe and S. Morooka, Nucleation and growth of diamond in a microwave plasma on substrate pretreated with non-oxide ceramic particles 121 (1992) 507
Mani, H., E. Tournié, J.L. Lazzari, C. Alibert, A. Joullié and B. Lambert, Liquid phase epitaxy and characterization of $InAs_{1-x-y}Sb_xP_y$ on (100) InAs 121 (1992) 463
Marzo, P., see Grange 121 (1992) 315
Masuda, S., see Maeda 121 (1992) 507
Masut, R.A., see Tran 121 (1992) 365
Matsumoto, S., see Okdada 121 (1992) 250
Matulenis, E.L., see Zayachuk 121 (1992) 235
Meekes, H., see Vogels 121 (1992) 697
Meng, Qingju, Baijun Chen, Guohua Hou, Lianmin Wu and Guang Dong, Modified hot wall epitaxy (HWE) apparatus and preparation of ZnS_xSe_{1-x} films 121 (1992) 191
Mikityuk, V.I., see Zayachuk 121 (1992) 235
Miotkowska, S., see Zytkiewicz 121 (1992) 457
Miyauchi, D., see Higuchi 121 (1992) 39
Moon, S.W., see Suh 121 (1992) 417
Moores, P.K., see Vere 121 (1992) 62
Moriguchi, Y., see Ichimura 121 (1992) 423
Moriyoshi, Y., see Okada 121 (1992) 250
Morooka, S., see Maeda 121 (1992) 507
Motakef, S., see Beda 121 (1992) 394
Müller, G., see Ostrogorsky 121 (1992) 587
Myerson, A.S, see Izmailov 121 (1992) 723

Nakajima, K., Calculation of stresses in GaAs/Si strained heterostructures 121 (1992) 278
Nanev, Chr.N. and R.St. Rashkov, Facet stability of crystals. I. Factors determining the polyhedral (in)-stability of silver single crystals during electrocrystallization at high current densities 121 (1992) 209
Nanev, Chr.N., Facet stability of crystals. II. Facet stability by impurity effects 121 (1992) 218
Narlikar, A.V., P.K. Dutta, S.B. Samanta and O.N. Srivastava, STM resolved step heights of growth spirals in $YBa_2Cu_3O_{7-y}$ crystals 121 (1992) 527
Naumann, R.J. and C. Baugher, Analytical estimates of radial segregation in Bridgman growth from low-level steady and periodic accelerations 121 (1992) 751
Neave, J.H., see Zhang 121 (1992) 381
Nishida, T., see Sugiura 121 (1992) 579

Obretenov, W. and V. Bostanov, Rate of crystal growth by 2D nucleation in the case of electrocrystallization of silver. II 121 (1992) 495
Okada, K., S. Komatsu, T. Ishigaki, S. Matsumoto and Y. Moriyoshi, Novel etching method for MgO {100} by using a combustion-flame 121 (1992) 250
Okada, M., see Yase 121 (1992) 449
Olszyna, A., see Sokołowska 121 (1992) 733
Orito, F., see Fujii 121 (1992) 255
Ostar, L.M., see Joyner 121 (1992) 413
Ostrogorsky, A.G., and G. Müller, A model of effective segregation coefficient, accounting for convection in the solute layer at the growth interface 121 (1992) 587
Otte, M., see Schlossmacher 121 (1992) 671
Oussena, M., see Gagnon 121 (1992) 559

Pan Peicong, Zhu Hongbin, Yan Shenhui, Chai Yiao, Wang Siting and Hou Yinchun, Distribution and valence of chromium in forsterite crystals grown by the Czochralski technique 121 (1992) 141
Pashley, D.W., see Zhang 121 (1992) 381
Peaker, A.R., see Poole 121 (1992) 121
Pollard, R., see Dabholkar 121 (1992) 71
Poole, I., K.E. Singer, A.R. Peaker and A.C. Wright, Growth and structural characterization of molecular beam epitaxial erbium-dopted GaAs 121 (1992) 121
Priecel, I., see Korytár 121 (1992) 440

Queisser, H.-J., see Lu 121 (1992) 566

Rashkov, R.St., see Nanev 121 (1992) 209
Razdan, A.K., see Bamzai 121 (1992) 519
Remy, F., J. Gastaldi, G. Grange, C. Jourdan and G. Le Lay, Synchrotron radiation white-beam X-ray transmission topography of mercuric iodide single crystals grown by vapor phase transport 121 (1992) 243
Richter, W., see Wright 121 (1992) 111
Rijpkema, J.J.M., see Bennema 121 (1992) 679
Ristić, R.I., see Bhat 121 (1992) 709
Roberts, K.J., see Bennema 121 (1992) 679
Rodríguez-Clemente, R., see Sandiumenge 121 (1992) 247
Rodríguez-Hornedo, N., see Li 121 (1992) 33
Rodway, D.C., see Vere 121 (1992) 62
Rüfer, H., see Schlossmacher 121 (1992) 671

Saito, Y., see Yase 121 (1992) 449
Salnick, Z.A., Oxygen in Czochralski silicon crystals grown under an axial magnetic field 121 (1992) 775
Samanta, S.B., see Narlikar 121 (1992) 527
Sandiumenge, F., S. Veintemillas-Verdaguer, R. Rodríguez-Clemente and S. Galí, Dipyramidal habit of flux-grown cobalt-tin doped barium ferrite 121 (1992) 247
Sasaki, A., see Ichimura 121 (1992) 423
Sasaki, T., see Yase 121 (1992) 449
Sato, K., see Yase 121 (1992) 449
Sato, T., see Fujii 121 (1992) 255
Schelb, S., see Stöber 121 (1992) 656

Schlak, M., see Beccard 121 (1992) 373
Schlossmacher, P., M. Otte, K. Urban and H. Rüfer, Identification of Zn–As phases in Zn-doped LEC-GaAs 121 (1992) 671
Schmald, R., see Beccard 121 (1992) 373
Sherwood, J.N., see Bhat 121 (1992) 709
Shieh, H.M., T.S. Wu and W.C. Hsu, SiH_4-doped AlGaAs epilayers formed by MOCVD 121 (1992) 665
Shimura, T., see Goto 121 (1992) 360
Shinohara, M., see Katsumata 121 (1992) 737
Shinohara, T., see Hoshizaki 121 (1992) 53
Shripathi, T., see Bhat 121 (1992) 709
Srivastava, O.N., see Narlikar 121 (1992) 527
Sides, P.J., see Snyder 121 (1992) 631
Singer, K.E., see Poole 121 (1992) 121
Škrtić, D., N. Filipović-Vinceković and V. Babić-Invančić, The effect of dodecylammonium chloride on crystal growth of calcium oxalate 121 (1992) 197
Smith, L.M., see Gerrard 121 (1992) 500
Smith, P.C., see Vere 121 (1992) 62
Snyder, D.W., P.J. Sides and E.I. Ko, On the rate and uniformity of CdTe deposition in an impinging jet reactor: numerical simulations 121 (1992) 631
Sokołowska, A. and A. Olszyna, Photon assisted chemical synthesis of E-BN 121 (1992) 733
Stöber, D., B.O. Hildmann, H. Böttner, S. Schelb, K.-H. Bachem and M. Binnewies, Chemical transport reactions during crystal growth of PbTe and PbSe via vapour phase influenced by AgI 121 (1992) 656
Strunk, H.P., see Hansson 121 (1992) 790
Su Genbo, see Li 121 (1992) 516
Sugiura, H., T. Nishida, R. Iga, T. Yamada and T. Tamamura, Facet growth of InP/InGaAs layers on SiO_2-masked InP by chemical beam epitaxy 121 (1992) 579
Suh, S.H., S.W. Moon, J.S. Kim, S.W. Lim, N.J. Kwak, H.K. Kim and J.M. Kim, Slider liquid phase epitaxial growth of $Hg_{0.8}Cd_{0.2}Te$, $Hg_{0.7}Cd_{0.3}Te$ and $Hg_{0.3}Cd_{0.7}Te$ with precise control of alloy compositions 121 (1992) 417
Sundgren, J.-E., see Håkansson 121 (1992) 399

Tabuchi, M., see Ichimura 121 (1992) 423
Tack, R.D., see Bennema 121 (1992) 679
Takahashi, I., see Goto 121 (1992) 360
Takahashi, K., see Katsumata 121 (1992) 737
Takei, K., see Katsumata 121 (1992) 737
Takeuchi, A., see Higuchi 121 (1992) 39
Tamamura, T., see Sugiura 121 (1992) 579
Tiller, W.A., see Uda 121 (1992) 93
Tiller, W.A., see Uda 121 (1992) 155
Tournié, E., see Mani 121 (1992) 463
Tran, C.A., R.A. Masut, P. Cova, J.L. Brebner and R. Leonelli, Growth and characterization of InP on silicon by MOCVD 121 (1992) 365
Tsiveriotis, K., see Lee 121 (1992) 536
Tsukamoto, K., see Cherepanova 121 (1992) 1

Uda, S. and W.A. Tiller, The influence of an interface electric field on the distribution coefficient of chromium in $LiNbO_3$ 121 (1992) 93
Uda, S. and W.A. Tiller, The dissociation and ionization of $LiNbO_3$ melts 121 (1992) 155
Urban, K., see Schlossmacher 121 (1992) 671
Usami, A., see Ichimura 121 (1992) 423

Van Landuyt, J., see Amelinckx 121 (1992) 543
Van Tendeloo, G., see Amelinckx 121 (1992) 543
Vanderwater, D.A., see Elliott 121 (1992) 349
Veintemillas-Verdaguer, S., see Sandiumenge 121 (1992) 247
Vekilov, P.G., Yu.G. Kuznetsov and A.A. Chernov, The effect of temperature on step motion; (101) ADP face 121 (1992) 44
Vekilov, P.G., Yu.G. Kuznetsov and A.A. Chernov, Interstep interaction in solution growth; (101) ADP face 121 (1992) 643
Verbeeck, R.M.H. and J.A.H. Devenyns, The kinetics of dissolution of octacalcium phosphate. II. The combined effects of pH and solution Ca/P ratio 121 (1992) 335
Vere, A.W., D.C. Rodway, K.J. Mackey, P.C. Smith and P.K. Moores, Photo-assisted growth of gallium arsenide 121 (1992) 62
Verheijen, M.A., see Vogels 121 (1992) 697
Vogels, L.J.P., see Cherepanova 121 (1992) 17
Vogels, L.J.P., M.A. Verheijen, H. Meekes and P. Bennema, The temperature and chemical composition dependence of the modulation wave vector in $((CH_3)_4N)_2ZnCl_{4-x}Br_x$ compounds determined from the morphology 121 (1992) 697

Wada, T., see Ichimura 121 (1992) 423
Wallenberg, L.R., see Håkansson 121 (1992) 399
Wan, C.C., see Chen 121 (1992) 322
Wang, Hailong, see Cui 121 (1992) 795
Wang Siting, see Pan 121 (1992) 141
Wang, T.G., see Grugel 121 (1992) 599
Wanklyn, B.M., see Bamzai 121 (1992) 519
Wermke, A., T. Boeck, T. Göbel and K. Jacobs, Thermodynamic investigations on the liquid phase epitaxy of $Hg_{1-x}Cd_xTe$ layers 121 (1992) 571
Westwood, D.I., see Clark 121 (1992) 743
Williams, J.O., see Wright 121 (1992) 111
Williams, R.H., see Clark 121 (1992) 743
Woodward, T., see Grugel 121 (1992) 599
Wright, A.C., J.O. Williams, A. Krost, W. Richter and D.R.T. Zahn, High resolu-

tion and conventional transmission electron microscopy of Ga_2Se_3 thin films grown by vapour phase epitaxy 121 (1992) 111
Wright, A.C., see Poole 121 (1992) 121
Wu Baichang, see Li 121 (1992) 516
Wu, Lianmin, see Meng 121 (1992) 191
Wu, T.S., see Shieh 121 (1992) 665

Yamada, T., see Sugiura 121 (1992) 579
Yamamoto, J.K., K. Kitamura, N. Iyi and S. Kimura, Sc_2O_3-doped $LiNbO_3$ grown by the float zone method 121 (1992) 522
Yamanaka, M., see Yase 121 (1992) 449
Yan Shenhui, see Pan 121 (1992) 141
Yang, J.R., C.K. Chung, W.J. Chen, Y.H. Chang and J. Hwang, Heteroepitaxy of PtSi/SiGe on Si(100) by dual electron gun co-deposition at high temperatures 121 (1992) 717
Yanson, Yu.A., see Cherepanova 121 (1992) 1
Yanson, Yu.A., see Cherepanova 121 (1992) 17
Yase, K., T. Sasaki, M. Yamanaka, T. Inoue, K. Inaoka, Y. Saito, C. Kaito, K. Sato and M. Okada, Initial stage of epitaxial growth mechanism of cadmium arachidate prepared by physical vapour deposition on various substrates 121 (1992) 449
Young, Byung-Chun, Characterization of anatase type $(Sn_xTi_{1-x})O_2$ solid solutions grown by CVD 121 (1992) 148

Zahn, D.R.T., see Wright 121 (1992) 111
Zayachuk, D.M., E.L. Matulenis and V.I. Mikityuk, The behaviour of Gd in lead and tin tellurides and its effect on their physical properties 121 (1992) 235
Zhang, J., see Zhang 121 (1992) 381
Zhang, J.H. and X.W. Fan, Surface process and lattice relaxation in growth of ZnS_xSe_{1-x} epilayers on GaAs substrate by VPE 121 (1992) 769
Zhang, X., D.W. Pashley, J.H. Neave, J. Zhang and B.E. Joyce, A transmission electron microscopy (TEM) study of a wedge-shaped InAs epitaxial layer on GaAs (001) grown by molecular beam epitaxy (MBE) 121 (1992) 381
Zhu Hongbin, see Pan 121 (1992) 141
Zotov, A.V. and V.G. Lifshits, Si solid phase epitaxy on Si–Sb and Si–B surface phases 121 (1992) 88
Zytkiewicz, Z.R. and S. Miotkowska, Compositional control of thick $Ga_{1-x}Al_xAs$ layers ($x \leq 0.72$) grown by liquid phase electroepitaxy 121 (1992) 457

Journal of Crystal Growth 121 (1992) 802–805
North-Holland

JOURNAL OF CRYSTAL GROWTH

Subject index

Alkali
– periodates 132
Alkanes 679
Alloys 315, 599
Aluminum
– copper alloy 315
– gallium arsenide 665
– organic 665
– oxide 473
Amino acids 33
Ammonium
– dihydrogen phosphate 44, 643
Apparatus
– for melt growth
– – by Bridgman–Stockbarger method
– – – in vertical mode
– – – – of garnets 473
– – – – of sapphire 473
– – by Czochralski method
– – – of gallium arsenide 349
– – by laser heated pedestal growth
– – – of lithium niobate 93
– – by traveling heater method
– – – of III–V compounds 305
– for solution growth
– – by flux method
– – – under pulsed laser
– – – – of boron nitride 733
– for thin film growth
– – by hot wall epitaxy
– – – of zinc chalcogenides 191
– – by liquid phase epitaxy
– – – of gallium aluminum arsenide 566
– – – using graphite button to control mercury loss
– – – – of mercury cadmium telluride 417
– – by vapor phase epitaxy
– – – through chemical beam deposition
– – – – using microwave plasma
– – – – – of diamond 507
– – – through metalorganic chemical vapor deposition
– – – – using jet reactor
– – – – – of cadmium telluride 631
– – – – using photoassistance
– – – – – of gallium arsenide 62
– for miscellaneous purposes
– – etching of magnesium oxide by combustion flame 250
– – measuring excitonic absorption 413

Barium
– hexaferrite 247
Bismuth
– strontium calcium cuprate 53
Boron
– nitride 733
Boundary layer control 93, 587
Brushite 297
Burton–Cabrera–Frank theory
– for glycine 33
Burton–Prim–Slichter model
– for determining partition coefficient 93, 587

Cadmium
– chelate 449
– indium telluride 202
– mercury telluride 417, 571
– telluride 631
Calcite 39
Calcium
– apatite 297, 335, 608, 617
– carbonate 39
– oxalate 197
– phosphates 297, 335, 608, 617
Cellular growth 315, 536
Characterization methods
– by absorption spectroscopy 62, 132, 522
– by Auger electron spectroscopy 223
– by cathodoluminescence 440, 579, 790
– by chemical analysis 522
– by deep level transient spectroscopy 255
– by differential scanning calorimetry 132
– by differential thermal analysis 155
– by electrical methods 93, 235, 255, 349, 373, 417, 463, 495, 559, 665
– by electron diffraction 381, 449, 543
– by electron microscopy 53, 62, 111, 121, 148, 191, 223, 235, 349, 381, 399, 423, 449, 457, 463, 507, 543, 559, 566, 579, 671, 679, 717, 733, 781, 790
– by electron probe microanalysis 53, 93, 463
– by electroreflectivity 394, 463
– by emission 769
– by ferroelectricity 132
– by inductively coupled plasma spectrometry 53
– by infrared transmission 417, 737
– by mass spectrometry 656
– by optical microscopy 39, 44, 53, 62, 132, 247, 255, 305, 349, 365, 531, 559, 566, 643, 781, 790
– by photoluminescence 191, 365, 463, 566, 665

- by Raman spectroscopy 423
- by reflection high energy electron diffraction 267, 717
- by scanning tunneling microscopy 527
- by secondary ion mass spectrometry 349, 373, 671
- by synchrotron radiation topography 243
- by transmission spectroscopy 413
- by X-ray methods 53, 93, 141, 148, 191, 202, 223, 240, 255, 315, 360, 365, 381, 399, 413, 423, 440, 463, 516, 522, 531, 679, 709, 717, 743, 769
- by X-ray photoelectron spectroscopy 62, 255

Computer simulation 71, 631
Constitutional supercooling 349
Convection 305, 322, 394, 473, 587, 751, 775
Copper 223
- aluminum 599

Dendritic growth 599
Diamond 507
Diffusional control 209, 218, 255, 394, 587, 656
Dislocations 247, 250, 278, 365, 399, 423, 440, 519, 543, 709, 743, 790
Dissolution
- of calcite 39
- of octacalcium phosphate 335

Distribution coefficient 93, 141, 235, 349, 522, 587
Dopants 93, 121, 235, 349, 373, 522, 656, 665, 671, 781

Etching
- chemical 349, 519, 781
- thermal 250

Finite element method 322
Forsterite 141
Fullerene 543

Gadolinium
- gallium garnet 473

Gallium
- aluminum arsenide 457, 566
- antimonide 305
- arsenide 62, 71, 121, 240, 255, 278, 305, 349, 423, 429, 440, 671
- organic 579
- selenide 111

Garnets 1, 17, 473
Germanium
- silicide 790

Glycine 33
Graphite 543

Heat flow control 93, 473
Heterojunction 278, 423

Impurity 88, 93, 218, 247, 656, 665, 737, 775
Indium
- antimonide 267
- arsenide 267, 381
- arsenide antimonide phosphide 463
- gallium arsenide 423, 579, 743
- gallium arsenide phosphide 413
- organic 500, 579
- phosphide 305, 365, 373, 429, 500, 579

Interface 88, 93, 111, 278, 381, 399, 413, 423, 473, 608, 617, 679, 743, 775

Kinetics
- of dissolution 335
- of growth 33, 39, 44, 71, 197, 209, 218, 235, 267, 305, 322, 399, 429, 608, 617, 643, 665, 679
- of interface control 1, 17, 566, 608, 617
- of nucleation 495, 608, 617, 723
- of species population change 155

Lattice mismatch 365, 463, 769
Lead
- copper alloy 599
- selenide 656
- telluride 235, 656

Lithium
- niobate 93, 155, 522
- tetraborate 737

Magnesium
- oxide 250
- silicate 141

Melt growth technique
- by Bridgman–Stockbarger method
- - of garnets 473
- - of lead telluride 235
- - of mercury manganese telluride 394
- - of sapphire 473
- - of tin telluride 235
- - theory of 473, 751
- by Czochralski method
- - of forsterite 141
- - of gallium antimonide.781
- - of gallium arsenide 240, 349, 671
- - under magnetic field
- - - of silicon 775
- by floating zone method
- - of lithium niobate 522
- by gradient freeze method
- - of gallium arsenide 255
- by laser heated pedestal growth
- - of lithium niobate 93
- by traveling heater method
- - of cadmium indium telluride 202
- by uniaxial solidification
- - of alloys 599
- - of aluminum copper alloy 315
- - of lithium tetraborate 737

Mercury
- cadmium telluride 417, 571
- (II) iodide 243

– manganese telluride 394
Microgravity 599, 723, 751
Molybdenum
– vanadium superlattices 399
Monte Carlo method 71, 429
Morphological stability 209, 218, 315, 697
Morphology of growth 1, 17, 33, 39, 71, 132, 247, 381, 417, 449, 543, 697, 790

Nonlinear optics 516
Nucleation 495, 507, 536, 608, 617, 723
Numbers
– Grashof 473
– Hartmann 305
– Peclet 322
– Rayleigh 305
– Reynolds 322, 631
– Schmidt 322, 631
– Sherwood 322, 631

Optoelectronic devices 413
Organic crystals 33, 516, 536, 679, 697

Perfection of crystals 39, 88, 235, 243, 315, 440, 516, 519, 536, 656, 709, 743, 781
Periodates
– alkali metal 132
Periodic bond chain theory 679
Phase diagrams
– of alkanes 679
– of boron nitrides 733
– of cadmium telluride/indium telluride 202
– of calcium apatite 297
– of indium arsenide antimonide phosphide 463
– of mercury cadmium telluride 571
– of tetramethylammonium, tetrachloro, bromo, zincate 697
Phenomenological theory 218, 723
Platinum
– silicide 717
Potassium
– alum 709
– aluminum sulphate, hydrate 709
Percursor 500

Quantum wells/size effects 413, 566, 579

Sapphire 473
Silicon 88, 775
Silver 209, 218, 495
Solid growth technique
– by recrystallization
– – of silicon 88
Solution growth technique
– by electrocrystallization
– – of silver 209, 218
– theory of 218
– by flux method
– – of barium hexaferrite 247
– – of yttrium barium cuprate 527, 531, 559
– – of yttrium iron garnet 1, 17
– – of yttrium orthoferrite 519
– by gel method
– – of alkali metal periodates 132
– by hydrothermal growth
– – of calcite 39
– by low temperature method
– – of ammonium dihydrogen phosphate 44, 643
– – of calcium apatite 617
– of calcium oxalate 197
– – of calcium phosphates 297, 335
– – of glycine 33
– – of organic crystals 516
– – of potash alum 709
– theory of 608
Statistical mechanics, molecular theory 1, 17, 679, 723
Stefan problem or moving boundary problem 473
Step 1, 17, 44, 527, 566
Strain 278, 399, 423
Stress calculations 278
Succinonitrile
– acetone binary system 536
Superconductivity 53, 527, 531, 559
– bulk 53, 527, 531, 559
– characterization 53, 527, 531, 559
– crystal chemistry 53, 531
– high T_c 53, 527, 531, 559
Supercooling, supersaturation 1, 17, 39, 297, 656, 679, 723
Superlattices 399
Surface processes, 1, 17, 71, 608, 617, 769
Surface structure 1, 17, 71, 88, 360, 559, 679

Thermodynamics 155, 255, 463, 571, 656, 679, 723
Thin film growth
– by chemical beam epitaxy
– – of gallium arsenide 429
– – of indium gallium arsenide 579
– – of indium phosphide 429, 579
– simulation of 429
– by electrocrystallization
– – of silver 495
– – theory of 495
– by hot wall epitaxy
– – of zinc chalcogenides 191
– by liquid phase electroepitaxy
– – of gallium aluminum arsenide 457
– by liquid phase epitaxy
– – of gallium aluminum arsenide 566
– – of germanium silicide 790
– – of indium arsenide antimonide phosphide 463
– – of mercury cadmium telluride 417, 571
– – theoretical simulation of 322
– by molecular beam epitaxy
– – of gallium arsenide 121, 423
– – of indium antimonide 267

– – of indium arsenide 267, 381
– – of indium gallium arsenide 423
– – of platinum silicide 717
– – of silicon 88
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of copper 223
– – – of diamond 507
– – – of gallium selenide 111
– – – of indium gallium arsenide 413
– – – of indium phosphide 373, 413
– – through evaporation and condensation
– – – of cadmium chelate 449
– – – of zinc sulphoselenide 769
– – through magnetron sputtering
– – – of molybdenum–vanadium superlattices 399
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 665
– – – of cadmium telluride 631
– – – of gallium arsenide 62
– – – of indium phosphide 365, 500
– theory of 71
Three–five (III–V) compounds 305, 322
Tin
– aluminum alloy 599
– telluride 235
– titanium oxide 148

Uniformity of growth 322, 417

Vapor growth technique
– by chemical transport
– – of lead selenide 656
– – of lead telluride 656
– – of mercury(II) iodide 243
– – of tin titanium oxide 148

Whisker growth
– of graphite 543

Yttrium
– aluminum garnet 17
– barium cuprate 527, 531, 559
– iron garnet 1, 17, 473
– orthoferrite 519

Zinc
– sulphoselenide 191, 769
Zincate
– tetramethyl ammonium, tetrachloro, bromo 697